

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	81	703/5[ccor]	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/10 15:26
L3	1072	438/106[ccor]	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/10 15:28
S1	1	10/054994	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/05 13:47
S3	1849	semiconduct\$4 and hydrostatic	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/05 13:53
S4	2	semiconduct\$4 and hydrostatic and "703"/\$[ccls]	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/08 12:52
S5	31	semiconduct\$4 and (material same stress) and "703"/\$[ccls]	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/05 13:50
S6	1208	703/14	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/05 13:50
S7	805	703/14[ccls]	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/05 13:50
S8	486	703/14[ccor]	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/05 13:50

S9	326	S7 and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/05 13:51
S11	327	S7 and semiconduc\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/05 13:51
S13	255	semiconduct\$4 same hydrostatic	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/05 13:53
S14	86	semiconduct\$4 with hydrostatic	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/05 13:54
S15	0	semiconduct\$4 with hydrostatic with simulate	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/05 13:54
S16	0	semiconduct\$4 with hydrostatic with simulat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/05 13:55
S17	0	(semiconduct\$4 with hydrostatic) same simulat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/05 14:28
S18	51	(semiconduct\$4 with physics) same simulat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/05 14:28
S19	308	(semiconduct\$4 with physic\$4) same simulat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/05 14:28
S20	18	hydrostatic\$3 near3 pressur\$3 same performance and simulation	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/08 13:05

S21	435	702/182[ccor]	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/08 13:06
S22	94	702/182[ccor] and @pd<"20011101"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/08 13:06
S23	0	702/182[ccor] and @pd<"20011101" and hydrostatic	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/08 13:07
S24	54	"702"/\$[ccor] and @pd<"20011101" and hydrostatic	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/08 13:07
S25	4	"702"/\$[ccor] and @pd<"20011101" and hydrostatic and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/08 13:10
S26	490	703/14[ccor]	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/08 13:10
S27	1	703/14[ccor] and hydrostatic	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/08 13:11
S28	1	703/14[ccls] and hydrostatic	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/08 13:11
S29	1	703/14[ccls] and hydrostat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/08 13:11
S30	40	703/14[ccls] and (stress strain)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/08 16:50

S31	21	703/14[ccls] and (stress strain) and display	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/08 16:52
S32	43	703/14[ccls] and (stress pressure strain) and display	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/08 16:53
S33	1	703/14[ccls] and (stress pressure strain) and display and hydrostatic	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/08 16:52
S34	22	S32 not S31	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/08 16:56
S35	498	hydrostat\$4 same simulat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/08 16:57
S37	12	hydrostat\$4 same simulat\$4 and soc	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/08 16:58
S38	6	(compre\$5 tensil\$4 tensio\$4) same semicondu\$4 same simulat\$4 same propert\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/08 17:01
S39	17	(compre\$5 tensil\$4 tensio\$4) with semicondu\$4 and (simulat\$4 same propert\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/08 17:02
S40	17	S39 not S37	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/08 17:02
S41	14	S39 not (S37 or S36)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/08 17:04

S42	257	semiconduc\$4 same hydrosta\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/08 17:05
S43	9	semiconduc\$4 same hydrosta\$4 and simulat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/08 17:07
S44	1844	semiconduc\$4 adj device same simulat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/08 17:07
S45	3	semiconduc\$4 adj device same simulat\$4 and hydrosta\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/08 17:15
S46	12	(substr\$4 semiconduc\$4) adj device same simulat\$4 and hydrosta\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/08 17:20
S47	130	vlsi and hydrostat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/08 17:21
S48	52	vlsi and hydrostat\$4 and simulat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/08 17:22
S49	20	vlsi and hydrostat\$4 and simulat\$4 not (ink near jet)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/08 17:24
S50	19	device\$4 with performanc\$4 same simulat\$4 and hydrostat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/07/10 15:24